

Title (en)  
LOW VOLTAGE SINGLE SUPPLY CMOS ELECTRICALLY ERASABLE READ-ONLY MEMORY

Title (de)  
CMOS ELEKTRISCH LÖSCHBARER, PROGRAMMIERBARER NUR-LESE-SPEICHER MIT ALLEINIGER NIEDERSPANNUNGSSPEISUNG

Title (fr)  
EEPROM CMOS A ALIMENTATION UNIQUE A FAIBLE TENSION

Publication  
**EP 0953211 A2 19991103 (EN)**

Application  
**EP 97954967 A 19971224**

Priority  

- US 9718800 W 19971224
- US 77831597 A 19970102
- US 89041597 A 19970709

Abstract (en)  
[origin: WO9829907A2] P channel EEPROM cells are designed for integration into arrays written with single polarity signals developed from small, low power charge pumps. These cells reduce the additional masking steps that must be added to a CMOS logic process for EEPROM to only one additional step. The novel cells of this invention enable the array to function with a Vpp about 2 V less than that required by an N channel EEPROM cell, with similar writing speed and tunnel oxide thickness.

IPC 1-7  
**H01L 27/00**

IPC 8 full level  
**G11C 16/04** (2006.01); **H01L 27/115** (2006.01)

CPC (source: EP US)  
**G11C 16/0433** (2013.01 - EP US); **H10B 69/00** (2023.02 - EP US)

Citation (search report)  
See references of WO 9829907A2

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**WO 9829907 A2 19980709; WO 9829907 A3 19980911**; AU 6129898 A 19980731; EP 0953211 A2 19991103; TW 376584 B 19991211; US 2002191439 A1 20021219; US 5986931 A 19991116; US 6574140 B2 20030603

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**US 9718800 W 19971224**; AU 6129898 A 19971224; EP 97954967 A 19971224; TW 86119774 A 19971226; US 73109900 A 20001205; US 89041597 A 19970709